

Single Ultra Fast Recovery Rectifier Diodes

Designed for use in switching power supplies inverters and as free wheeling diodes. These state-of-the-art devices have the following

Features

- *High Surge Capacity
- *Low Power Loss, High efficiency
- *150 °C Operating Junction Temperature
- *Low Stored Charge Majority Carrier Conduction
- *Low Forward Voltage, High Current Capability
- *High-Switching Speed Recovery Time
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O
- * Pb free
- * In compliance with EU RoHs directives



MAXIMUM RATINGS

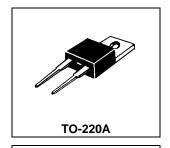
Characteristic	Symbol	UE08A60	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	600	V
RMS Reverse Voltage	V _{R(RMS)}	420	٧
Average Rectifier Forward Current Total Device (Rated V _R), T _C =100°C	I _{F(AV)}	8	А
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz)	I _{FM}	8	А
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	I _{FSM}	100	А
Operating Junction and Storage Temperature Range	T_J , T_stg	-65 to +150	$^{\circ}\!\mathbb{C}$

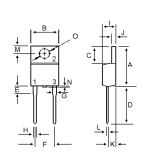
ELECTRICAL CHARACTERISTICS

ELECTRICAL CHARACTERISTICS						
Characteristic	Symbol	Min.	Тур.	Max.	Unit	
Maximum Instantaneous Forward Voltage ($I_F = 8.0 \text{ Amp } T_C = 25^{\circ}C$) ($I_F = 8.0 \text{ Amp } T_C = 125^{\circ}C$)	V _F		1.30 1.15	1.60 	V	
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C = 25^{\circ}C$) (Rated DC Voltage, $T_C = 125^{\circ}C$)	I _R		0.01 10	10 	uA	
Reverse Recovery Time ($I_F = 0.5 \text{ A}$, $I_R = 1.0$, $I_{rr} = 0.25 \text{ A}$)	T _{rr}		27	50	ns	
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	СР		28		₽F	

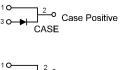
ULTRA FAST RECTIFIERS

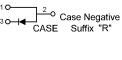
8 AMPERES 600 VOLTS



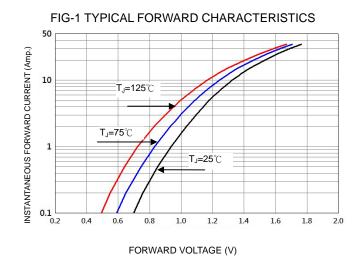


DIM	MILLIMETERS		
DIIVI	MIN	MAX	
Α	14.68	16.00	
В	9.78	10.42	
С	5.02	6.60	
D	13.00	14.62	
E	3.10	4.19	
F	4.82	5.34	
G	1.10	1.67	
Н	0.69	1.01	
- 1	4.22	4.98	
J	1.14	1.40	
K	2.20	3.30	
L	0.28	0.61	
M	2.48	3.00	
N		2.00	
0	3.50	4.00	

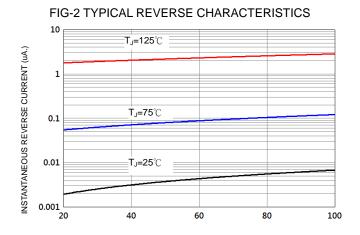




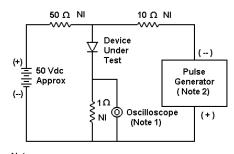








PERCENT OF RATED PEAK REVERSE VOLTAGE (%)



1. Rise Time = 7 ns max. Input Impedance =1 M Ω , 22 pF

2. Rise Time = 10 ns max. Input Impedance = 50 Ω

FIG-3 FORWARD CURRENT DERATING CURVE

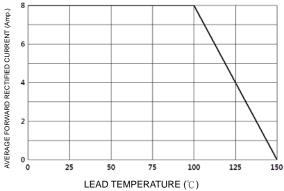
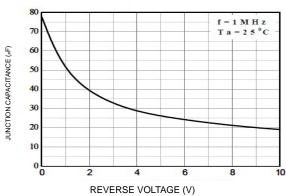
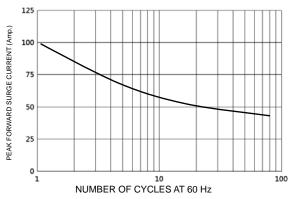
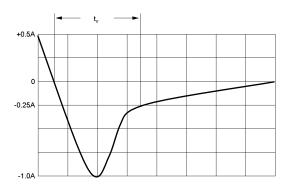


FIG-4TYPICAL JUNCTION CAPACITANCE









Set time base for 10/20 ns/cm

FIG-6 Reverse Recovery Time Characteristic and Test Circuit Diagram



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